Messrs. Rockwell Automation Co.,Ltd.

SPECIFICATION

Device Name : IGBT

Type Name : 1MBH03D-120-S06TT

Spec. No. : MS5F-4088

Date : June-11-1998

Fuji Electric Co.,Ltd.
Matsumoto Factory

	DATE	NAME	APPROVED
DRAWN	June-11-98	K. Sawada	
CHECKED	June-11-98	T. Ogawashi	

Fuji Electric Co.,Ltd.

DWG.NO. MS5F4088 1/14

Revised Records

Date	Classi-fication	Ind.	Content	Applied date	Drawn	Checked	Approved
July-15-1997	enactment	——	————	Issued date	——		
June-11-1998	Alteration	a	Alteration of packing specification. (3/14). and type name (1/14).	June-11-1998	K. Suzuki	T. Igarashi	

· Scope

This specification is applied to Fuji discrete IGBT 1MBH03D-120
supplied for Rockwell Automation Co.,Ltd.

· Construction

1. Package dimension
   There is a package dimension in 4/14 page .

2. Outview
   There are no remarkable flaws on a product .

3. Indication
   ① Tradmark
   ② Type Name
   ③ Lot No.

· Ratings and Characteristics

1. There are some ratings and characteristics tables in 4/14 page and 5/14 page .

2. There are some performance curves in from 6/14 page to 14/14 page .

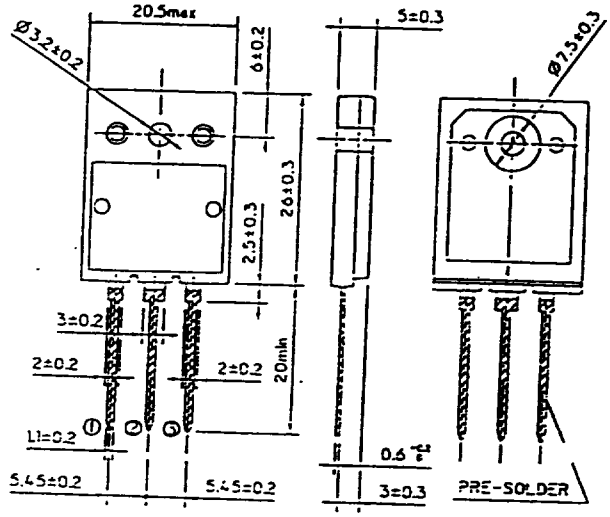
· Packing

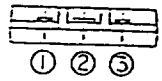
Packing style follows our packing specification ~~MS500026~~
MS5aa030 ②

Ratings and characteristics of Fuji IGBT

1MBH03D-120

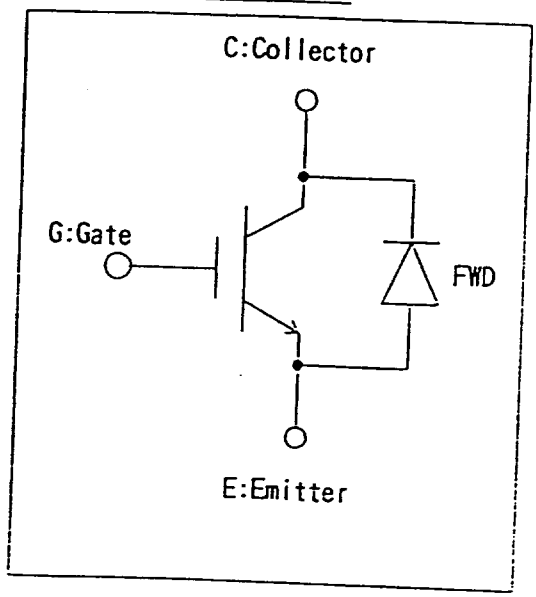
1. Outline Drawing





CONNECTION
① GATE
② COLLECTOR
③ EMITTER

2. Equivalent circuit



3. Absolute maximum ratings (Tc=25℃)

Items			Symbols	Ratings	Units
Collector-Emitter Voltage			V_{CES}	1200	V
Gate-Emitter Voltage			V_{GES}	±22	V
Collector Current	DC	Tc=25 ℃	Ic_{25}	5.5	A
		Tc=105℃	Ic_{105}	2.5	A
	1ms	Tc=25 ℃	Icp	15	A
IGBT Max. Power Dissipation			Pc	80	W
FWD Max. Power Dissipation			Pc	50	W
Operating Temperature			Tj	+ 150	℃
Storage Temperature			Tstg	-40 ~ +150	℃
Mounting Screw Torque			——	70	N・cm

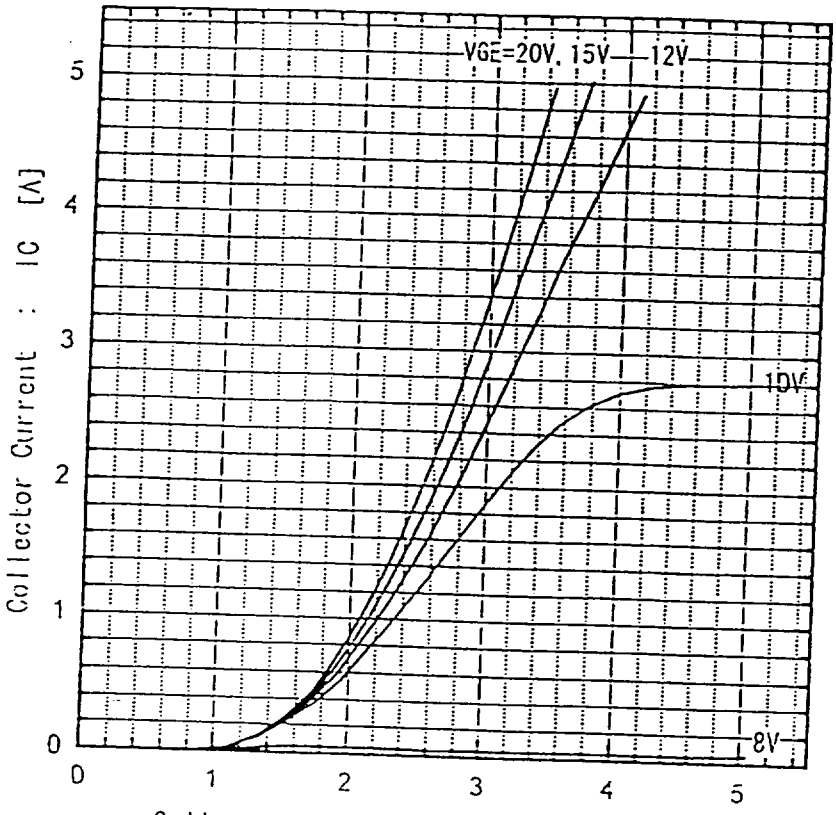
4. Electrical Characteristics (at Tc=25℃ unless otherwise specified)

Items		Symbols	Characteristics min.	Characteristics typ.	Characteristics max.	Conditions	Unit
Zero gate voltage Collector Current		I_{CES}			1.0	V_{GE} = 0V V_{CE} =1200V	mA
Gate-Emitter leakage Current		I_{GES}			20	V_{CE} = 0V V_{GE} = ±22V	μA
Gate-Emitter Threshold Voltage		$V_{GE(th)}$	5.5		8.5	V_{CE} = 20V Ic = 2.5mA	V
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$			3.5	V_{GE} = 15V Ic = 2.5A	V
Input capacitance		Cies		400		V_{GE} = 0V V_{CE} = 10V f = 1MHz	pF
Output capacitance		Coes		70			
Reverse transfer capacitance		Cres		20			
Switching Time	Turn-on time	ton			1.2	Vcc = 600V Ic = 2.5A V_{GE} = ±15V R_G = 430Ω (Half Bridge)	μs
		tr			0.6		
	Turn-off time	toff			1.5		
		tf			0.5		
	Turn-on time	ton		0.16		Vcc = 600V Ic = 2.5A V_{GE} = +15V R_G = 43 Ω (Half Bridge)	
		tr		0.11			
	Turn-off time	toff		0.30			
		tf			0.50		
FWD forward voltage drop		VF			3.0	I_F =2.5A	V
Reverse recovery time		trr			0.35	IF=2.5A, VGE=-10V VR= 200V di/dt=100A/μs	μs

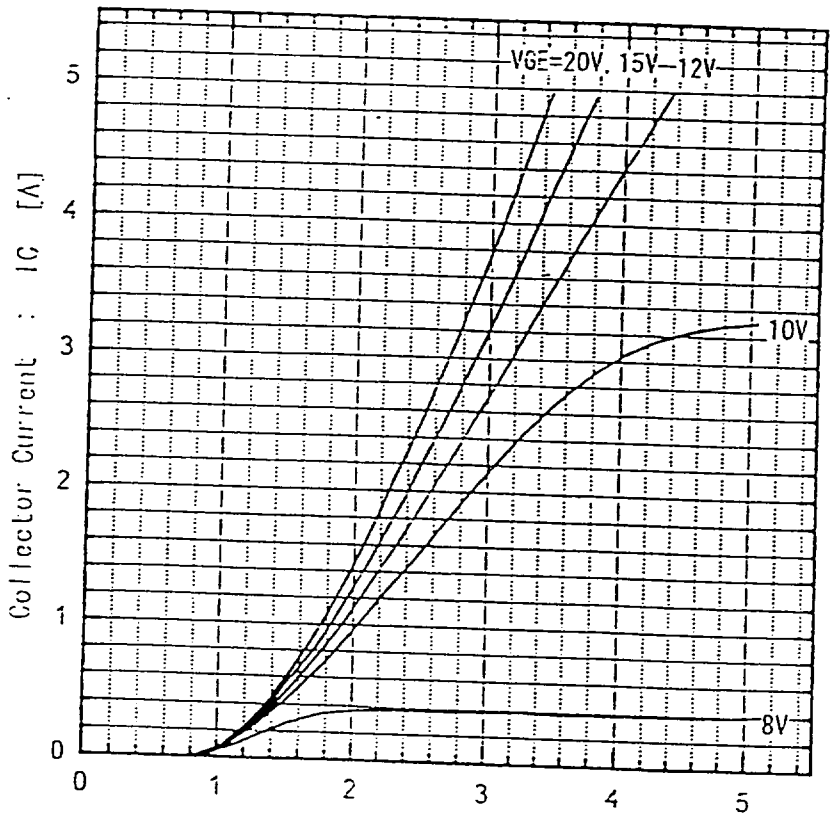
5. Thermal resistance characteristics

Items	Symbols	Characteristics min.	Characteristics typ.	Characteristics max.	Conditions	Unit
Thermal resistance	Rth(j-c)			1.56	IGBT	℃/W
	Rth(j-c)			2.50	FWD	

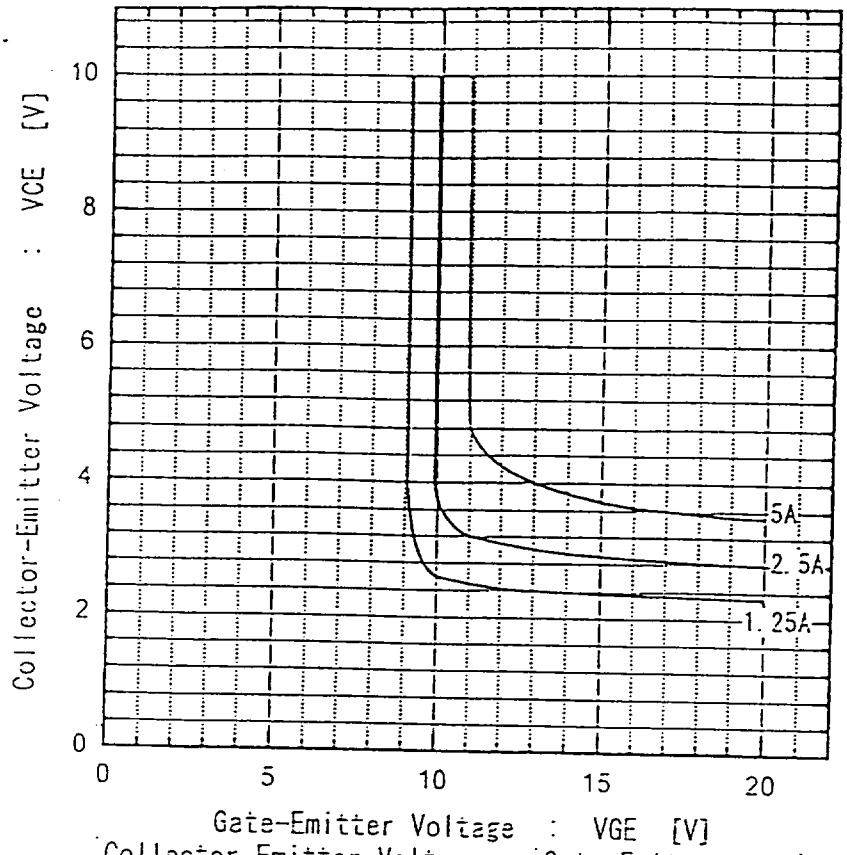
Collector Current vs. Collector-Emitter Voltage
Tj=25℃



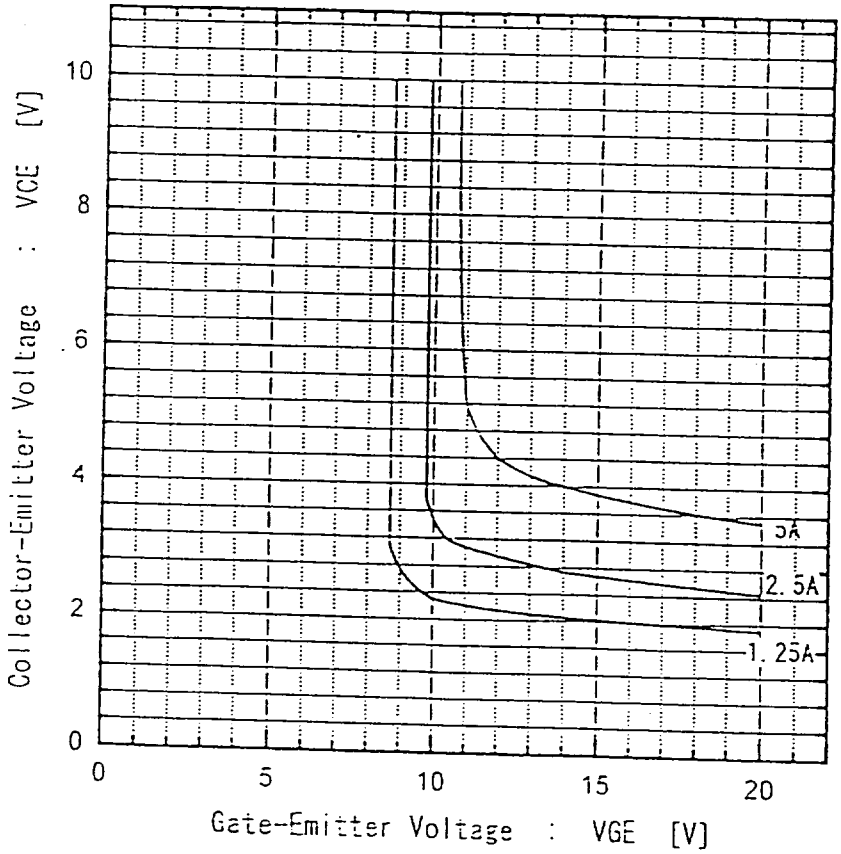
Collector Current vs. Collector-Emitter Voltage
Tj=125℃



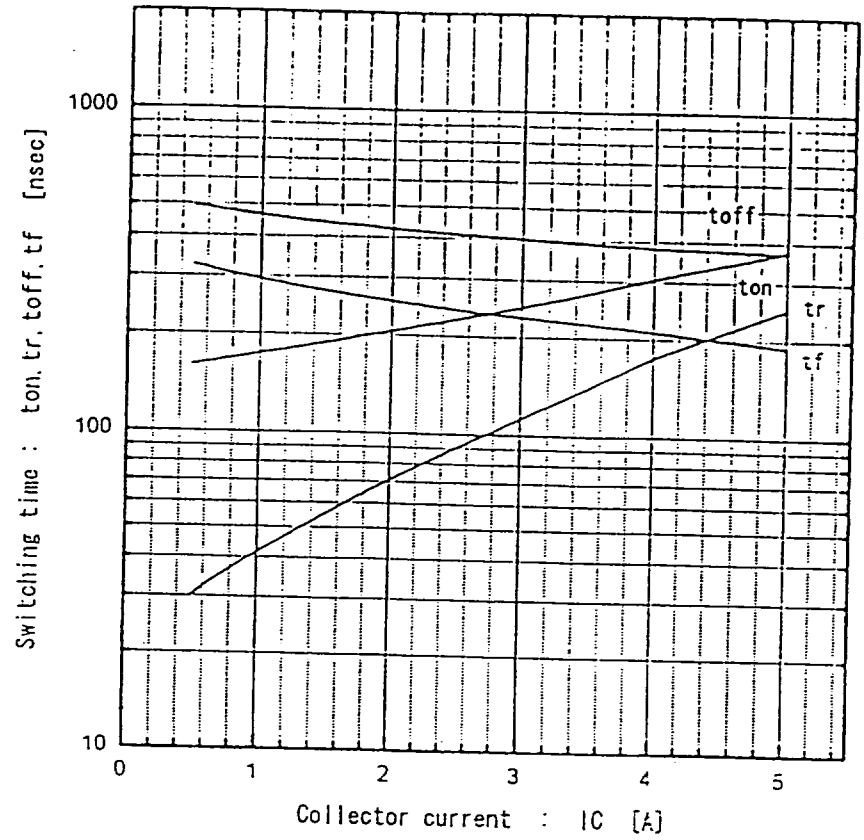
Collector-Emitter Voltage vs Gate-Emitter Voltage
Tj=25℃



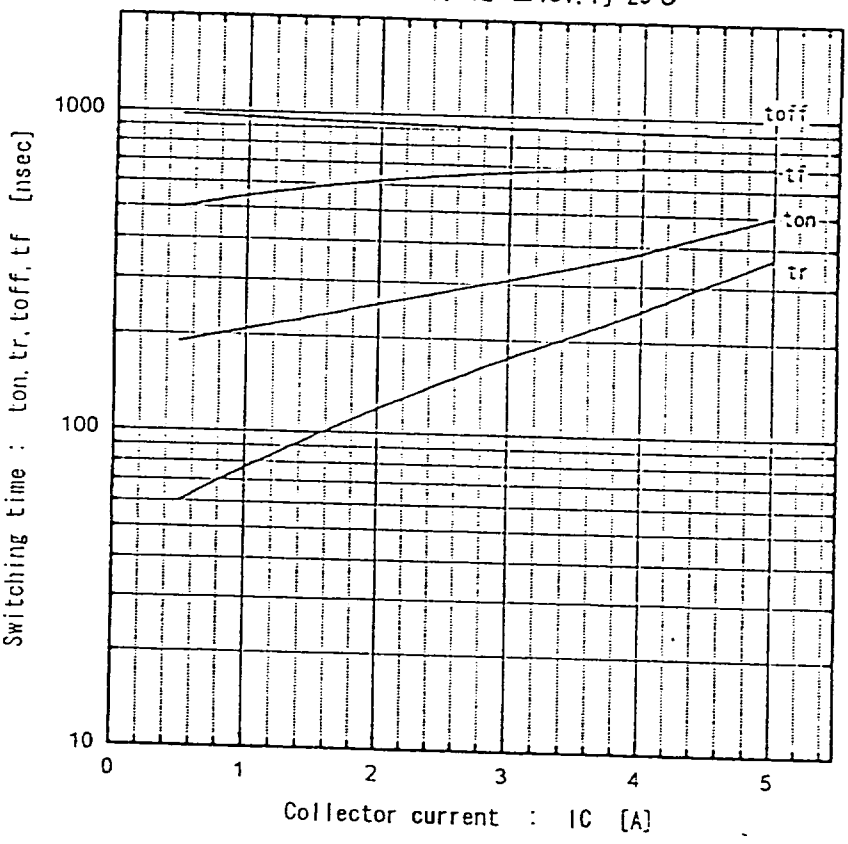
Collector-Emitter Voltage vs Gate-Emitter Voltage
Tj=125℃



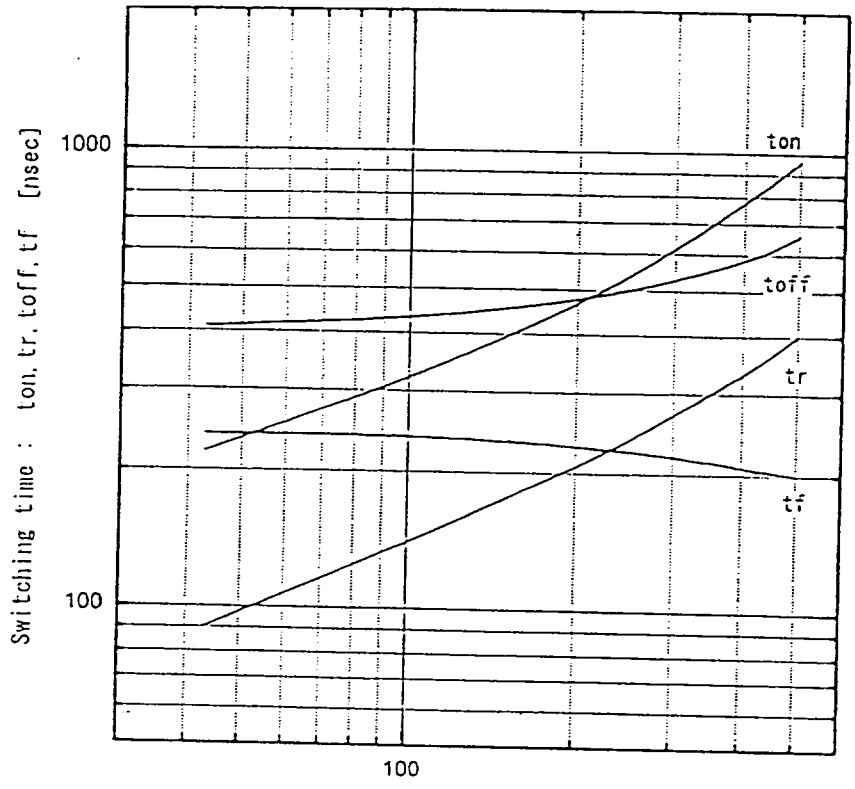
Switching time vs. Collector current
Vcc=600V, RG=43Ω, VGE= ±15V, Tj=25°C



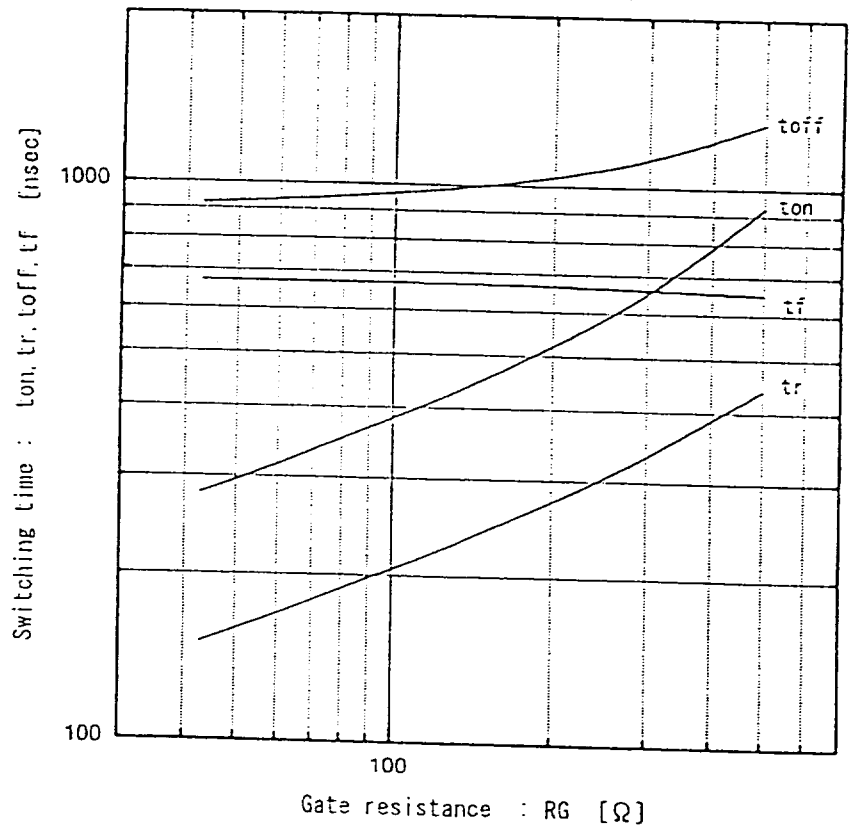
Switching time vs. Collector current
Vcc=600V, RG=43Ω, VGE= ±15V, Tj=25°C



Switching time vs. RG
Vcc=600V. IC=2. 5A. VGE=±15V. Tj=25°C

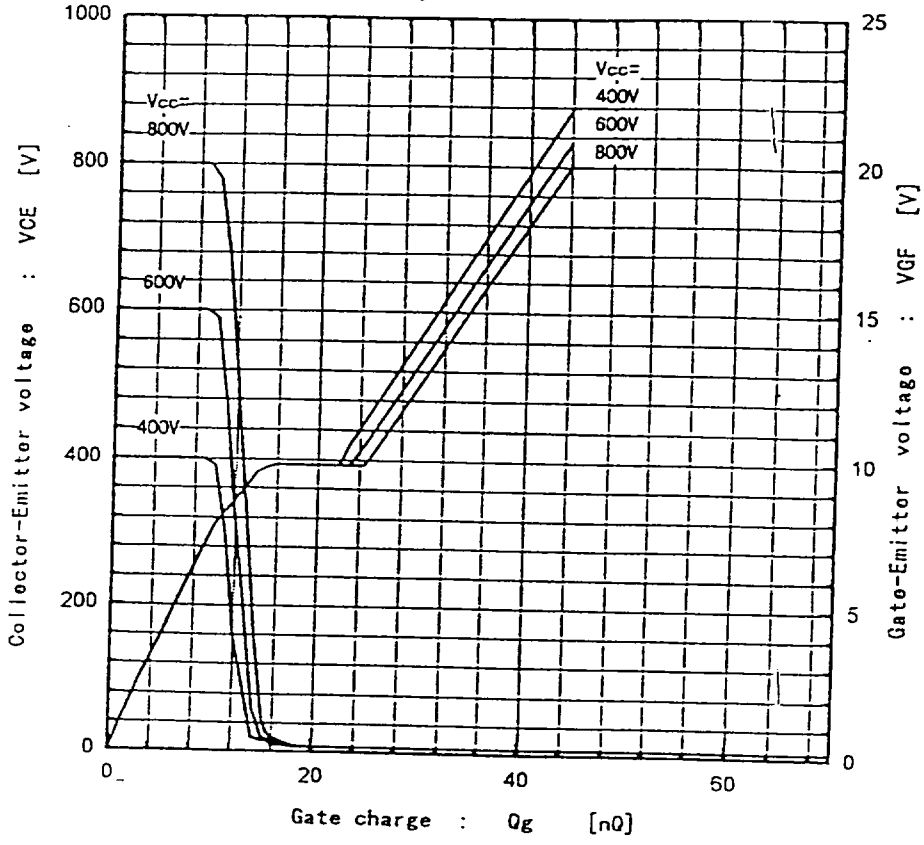


Switching time vs. RG
Vcc=600V. IC=2. 5A. VGE=±15V. Tj=125°C



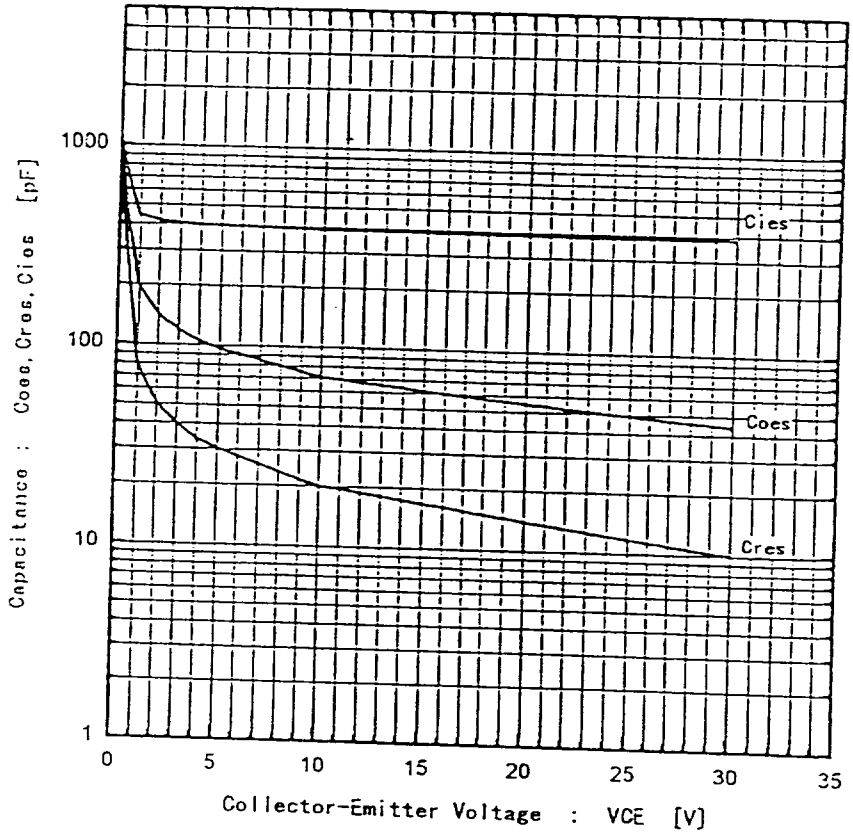
Dynamic input characteristics

Tj=25℃



Capacitance vs. Collector-Emitter voltage

Tj=25℃



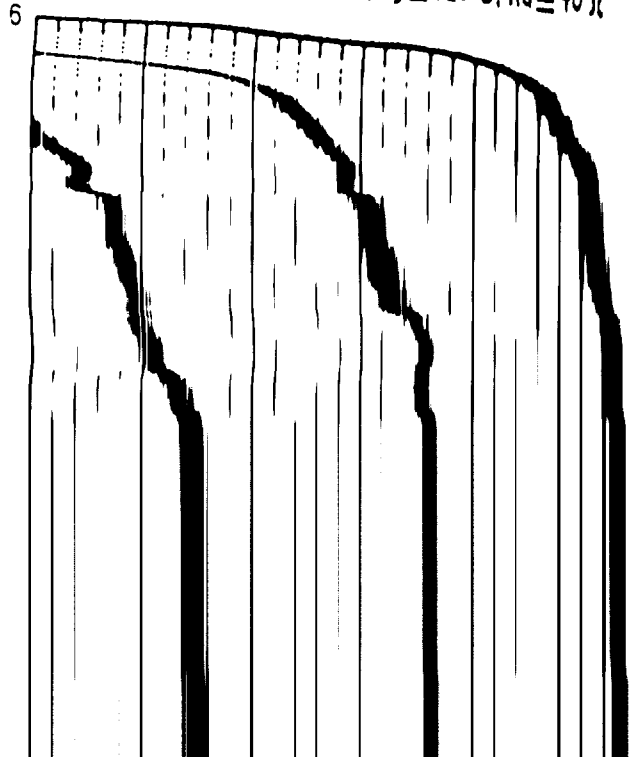
Fuji Electric Co.,Ltd.

DWG.NO. MS5F4068

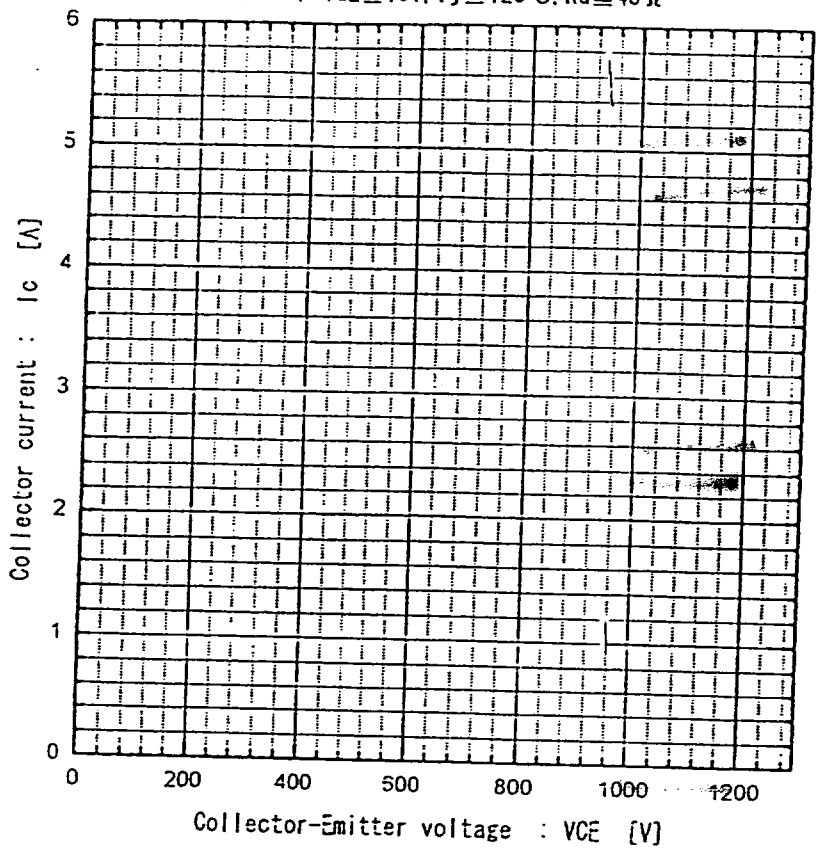
10/14

H04-004-03

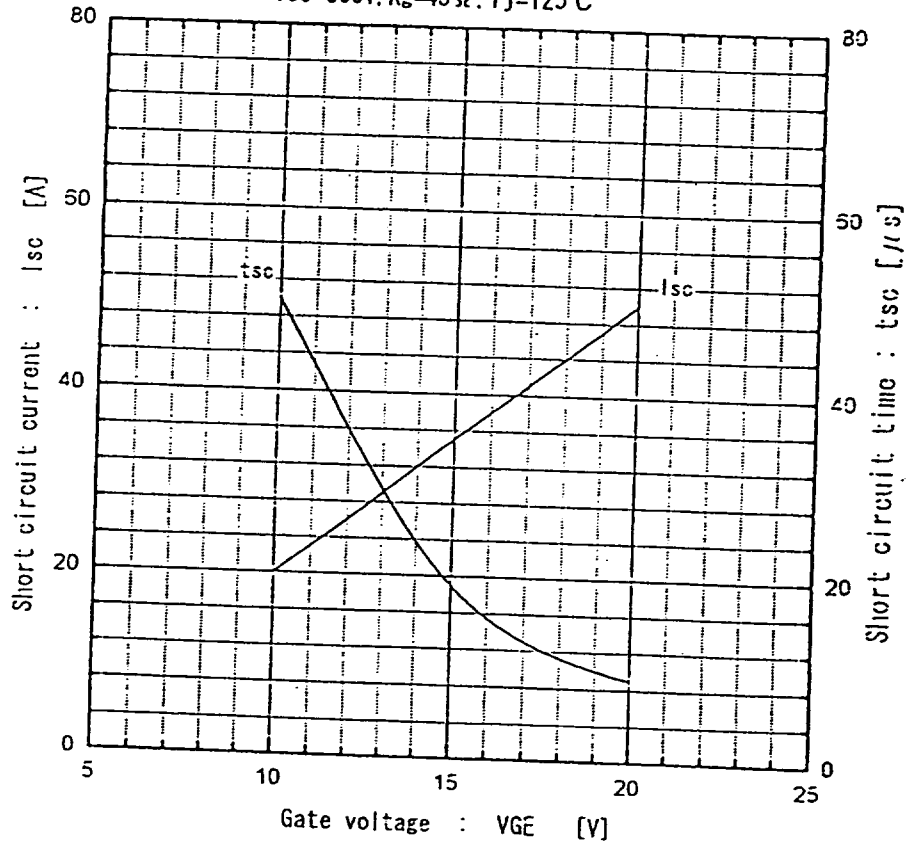
Reverse Biased Safe Operating Area
+VGE=15V, -VGE≦15V, Tj≦125°C, RG≧43Ω



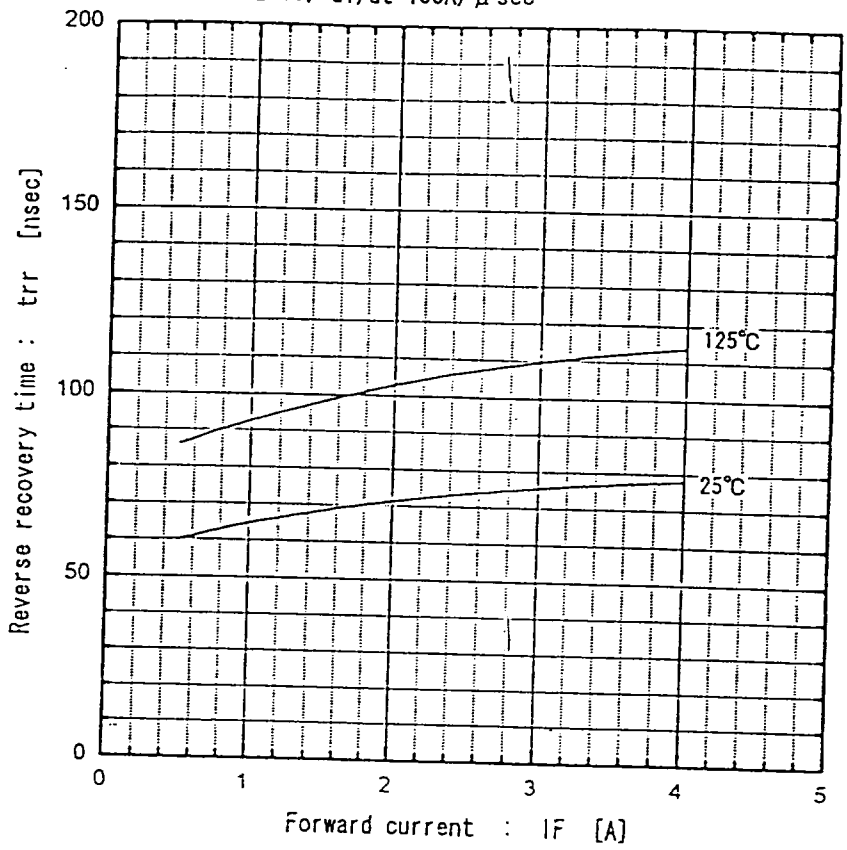
Reverse Biased Safe Operating Area
+VGE=15V, -VGE≦15V, Tj≦125°C, RG≧43Ω



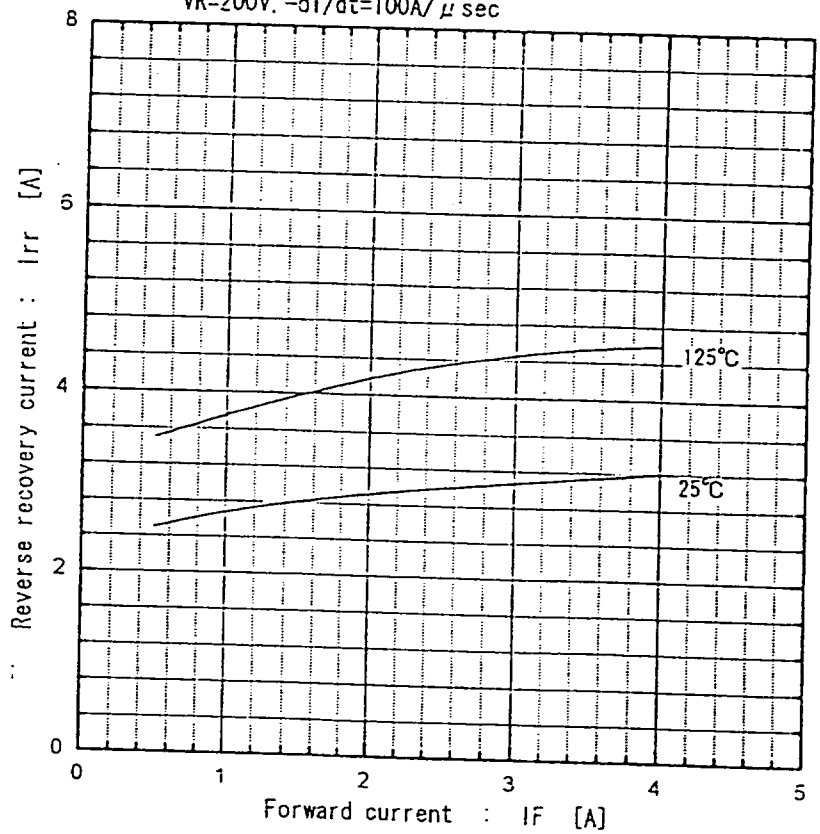
Typical short circuit capability
Vcc=800V, Rg=43Ω, Tj=125°C



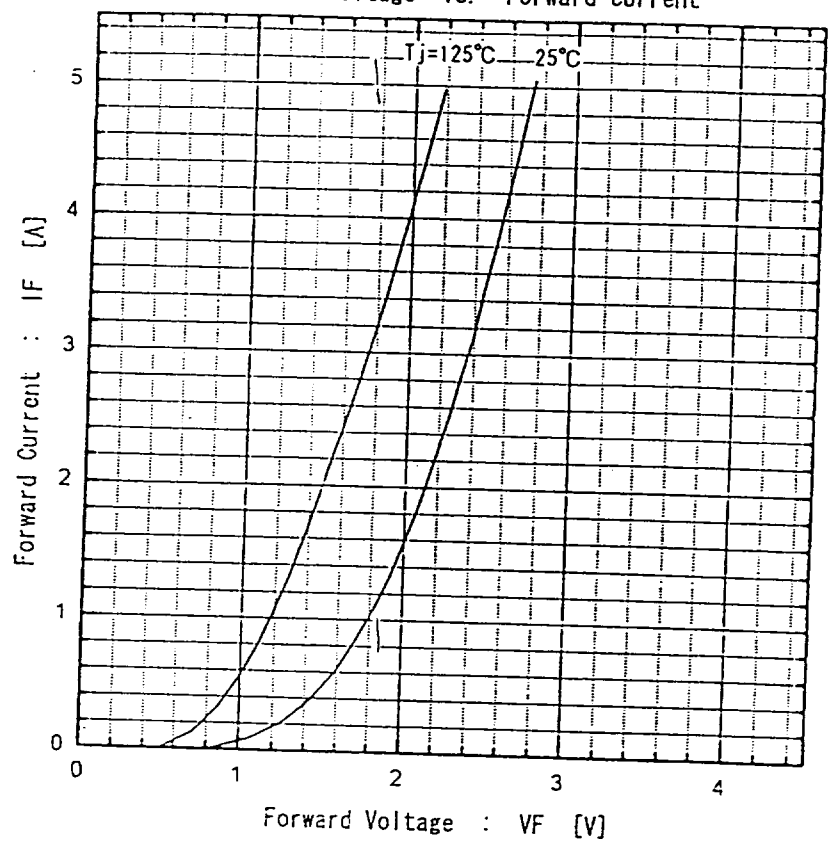
Reverse recovery time vs. Forward current
VR=200V. -di/dt=100A/μsec



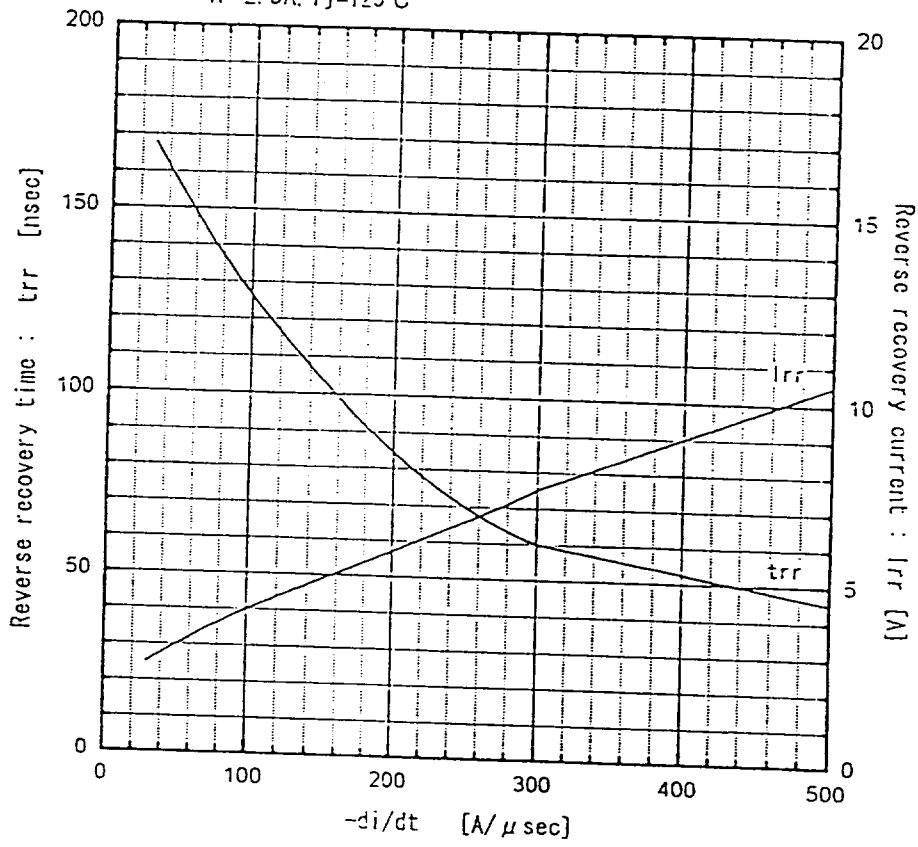
Reverse recovery current vs. Forward current
VR=200V. -di/dt=100A/μsec



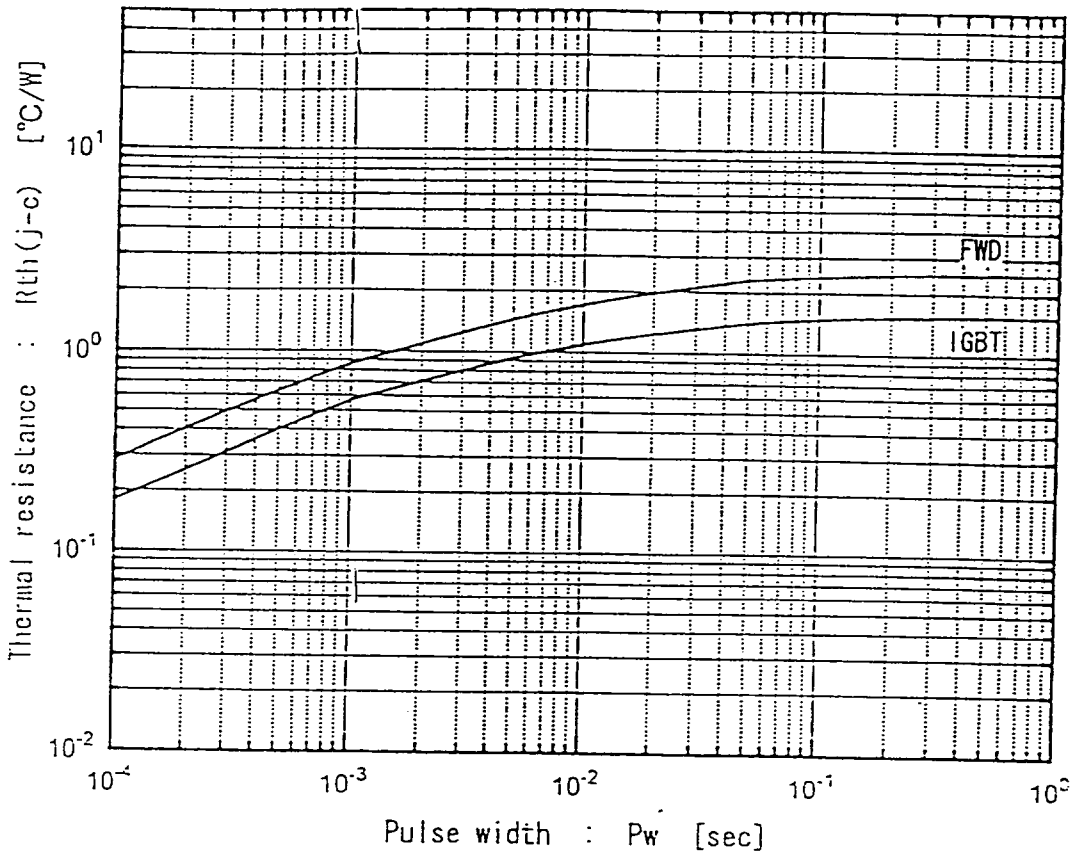
Forward voltage vs. Forward current



Reverse recovery chracteristics vs. -di/dt
IF=2.5A, Tj=125°C



Transient thermal resistance



Fuji Semiconductor, Inc. - P.O. Box 702708 - Dallas, TX 75370 - 972-733-1700
www.fujisemiconductor.com